

BASiC

B1D06065KS

MGT **A** Manufacturer Group of Technology

650V 🛦 6A 🛦 SIC SCHOTTKY DIODE

SILICON CARBIDE SIC SCHOTTKY DIODE ▲ THT type Excellent surge capability Easy paralleling due to positive V_F temperature coefficient Temperature independent switching Low forward voltage

TO-220 ISO-2L ceramic package ▲ 2.5kV isolation voltage





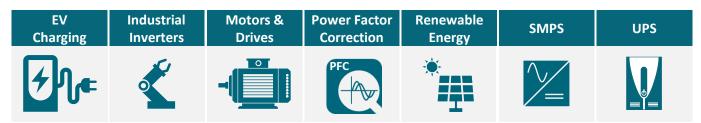
HALOGEN

FREE

SPECIFICATION

Item (T _c = 25°C, unless otherwise noted)	Characteristics	
Operating Temperature Range	TJ	-55°C to +175°C
Storage Temperature Range	Ts	-55°C to +175°C
Repetitive Peak Reverse Voltage	V _{RRM}	650V
Continuous Forward Current at T _c = 150°C	IF	6A
Total Capacitive Charge (TJ = 25°C)	Qc	17nC
Capacitance Stored Energy ($V_R = 400V$)	Ec	4.5µJ
Diode Forward Voltage (T _J = 175°C, I_F = 6A)	VF	1.75V
Power Dissipation	Ρτοτ	70W

APPLICATIONS



PIN DESCRIPTION

Circuit Diagram	Outline - Front View	Pin No.	Description
		1 2	Cathode Anode

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ABSOLUT MAXIMUM RATINGS A T_c = 25°C, unless otherwise noted

ltem	Condition	Symbol		Unit
Repetitive Peak Reverse Voltage		V _{RRM}	650	V
Non-Repetitive Peak Reverse Voltage		V _{RSM}	650	V
Continuous Forward Current	T _C = 25°C	IF	18	А
Continuous Forward Current	T _C = 150°C	IF	6	А
Non-Repetitive Forward Surge Current	T_{C} = 25°C, t_{p} = 10ms, Half Sine Wave	I _{FSM}	45	А
I ² t Value	T _C = 25°C, t _p = 10ms	∫i²dt	10.12	A ² s
Power Dissipation	T _C = 25°C	P _{TOT}	70	W
Power Dissipation	T _C = 110°C	P _{TOT}	30	W
Operating Junction Temperature		TJ	-55 to +175	°C
Storage Temperature Range		T _{STG}	-55 to +175	°C
Isolation Voltage	AC, t = 1s	VISOL	2500	V _{RMS}
TO-220 Mounting Torque	M3 Screw		0.7	Nm

ELECTRICAL CHARACTERISTICS

ltem	Condition	Symbol	Min.	Тур.	Max.	Unit
Static Characteristics						
DC Blocking Voltage	T _J = 25°C	V_{DC}	650			V
Diode Forward Voltage	I _F = 6A, T _J = 25°C	V _F		1.44	1.60	V
Diode Forward Voltage	I _F = 6A, T _J = 175°C	V _F		1.75	2.20	V
Reverse Current	V _R = 650V, T _J = 25°C	I _R		1	60	μΑ
Reverse Current	V _R = 650V, T _J = 175°C	I _R		20	200	μA
Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Dynamic Characteristics						
Total Capacitive Charge	$V_{R} = 400V, T_{J} = 25^{\circ}C$ $Q_{C} = \int_{0}^{V_{R}} C(V) dV$	Q _c		17		nC
Total Capacitance	V _R = 1V, f = 1MHz, T _J = 25°C	С		271		pF
Total Capacitance	V _R = 300V, f = 1MHz, T _J = 25°C	С		30.1		рF
Total Capacitance	V _R = 600V, f = 1MHz, T _J = 25°C	С		29.8		рF
Capacitance Stored Energy	V _R = 400V, T _J = 25°C	Ec		4.5		μ

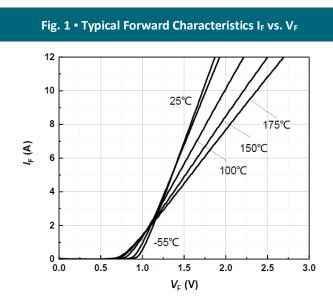
THERMAL RESISTANCE PERFORMANCE

Item	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance, Junction to Case	$R_{\theta,JC}$		2.117		K/W

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REFERENCE DATA A TYPICAL PERFORMANCE



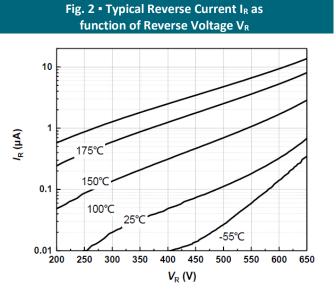
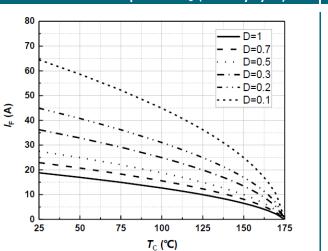


Fig. 3 • Diode Forward Current I_F as function of Case Temperature T_c (D = Duty Cycle)

Fig. 4 - Typical Capacitance C as function of



Reverse Voltage V_R , C =f(V_R), T_J = 25°C, f = 1MHz

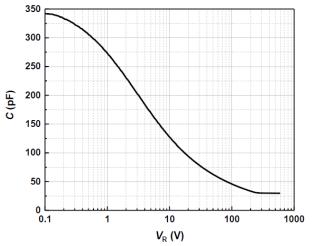


Fig. 5 • Typical Reverse Charge Q_c as function of Reverse Voltage V_R

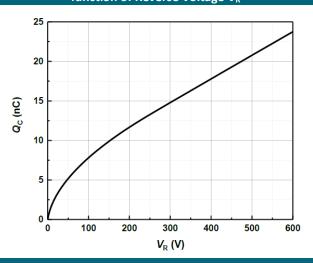
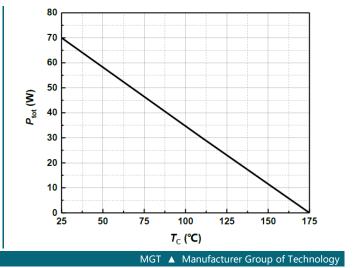


Fig. 6 • Power Dissipation P_{TOT} as function of Case Temperature T_c

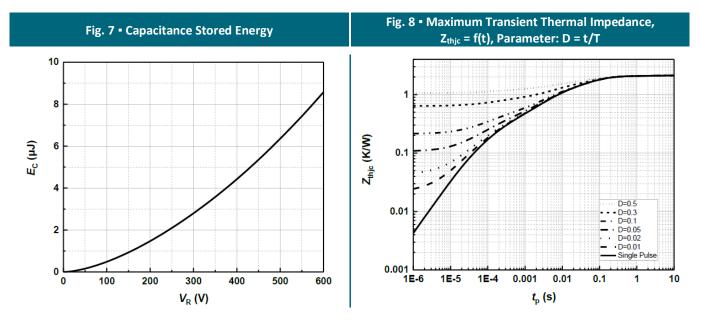


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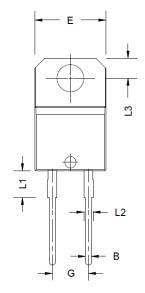


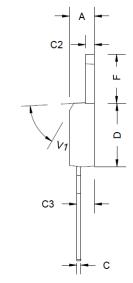
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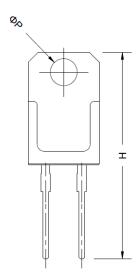




PACKAGE OUTLINE







|--|--|

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)	Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
А	4.40	4.50	4.60	G		5.08 BSC	
В	0.61	0.75	0.88	н	28.00	28.90	29.80
С	0.46	0.58	0.70	L1	-	3.75	-
C2	1.21	1.265	1.32	L2	1.14	-	1.70
C3	2.40	2.56	2.72	L3	2.65	2.80	2.95
D	8.60	9.15	9.70	V1	-	45°	-
E	9.80	10.10	10.40	ØР	-	-	3.88
F	6.55	6.75	6.95				

TO-220 ISO-2L package ▲ Epoxy meets UL94-V0

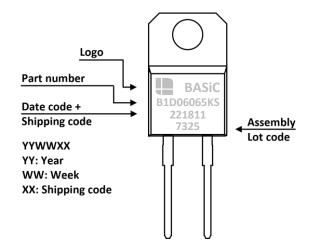
ORDERING INFORMATION

Part Number	Package	Packing	Tube Qty.	Inner Box Qty.	Outer Box Qty.
B1D06065KS	TO-220 ISO-2L	Tube	50pcs	500pcs	5,000pcs

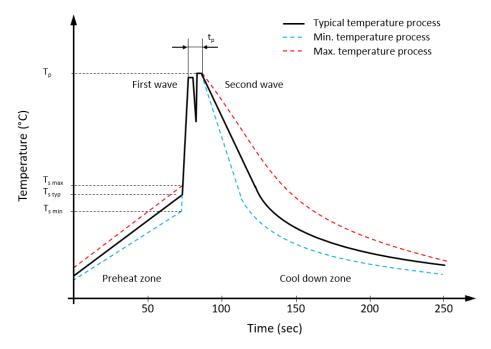
SILICON CARBIDE (SiC) SCHOTTKY DIODE ▲ B1D06065KS

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PART MARKING



RECOMMENDED WAVE SOLDERING PROFILE ▲ THT PACKAGE



Classification wave soldering profile ▲ Refer to EN 61760-1: 2006

Profile Features		Value 🛦 Sn-Pb Assembly	Value A Pb-free Assembly
Preheat temperature min.	T_{smin}	100 °C	100 °C
Preheat temperature typical	T _{s typ}	120 °C	120 °C
Preheat temperature max.	$T_{s max}$	130 °C	130 °C
Preheat time t_s from $T_{s min}$ to $T_{s max}$	ts	70 seconds	70 seconds
Peak temperature	Τ _p	235 °C to 260 °C	245 °C to 260 °C
Time of actual peak temperature	tp	Max. 10 seconds Max. 5 second each wave	Max. 10 seconds Max. 5 second each wave
Ramp-down date min.		~ 2 °C/second	~ 2 °C/second
Ramp-down rate typical		~ 3.5 °C/second	~ 3.5 °C/second
Ramp-down rate max.		~ 5 °C/second	~ 5 °C/second
Time 25°C to 25°C		4 minutes	4 minutes
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REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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